

**Document Title****512Kx8 bit Low Power and Low Voltage CMOS Static RAM****Revision History**

<b><u>Revision No.</u></b>	<b><u>History</u></b>	<b><u>Draft Data</u></b>	<b><u>Remark</u></b>
0.0	Initial draft	December 17, 1996	Preliminary
1.0	Finalize - Change datasheet format - Erase low power part from product - Erase 70ns part from KM68U4000B family - Power dissipation Improved 0.7 to 1.0W - $V_{IL(MAX)}$ improved 0.4 to 0.6V. - $I_{CC2}$ decreased 50 to 45mA.	January 14, 1998	Final
2.0	Revised - $I_{CC1}$ decreased 20 to 25mA	February 12, 1998	Final

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## 512K×8 bit Low Power and Low Voltage CMOS Static RAM

### FEATURES

- Process Technology : TFT
- Organization : 512K×8
- Power Supply Voltage
  - KM68V4000B Family : 3.0~3.6V
  - KM68U4000B Family : 2.7~3.3V
- Low Data Retention Voltage : 2V(Min)
- Three state output and TTL Compatible
- Package Type : 32-SOP, 32-TSOP2-400F/R

### GENERAL DESCRIPTION

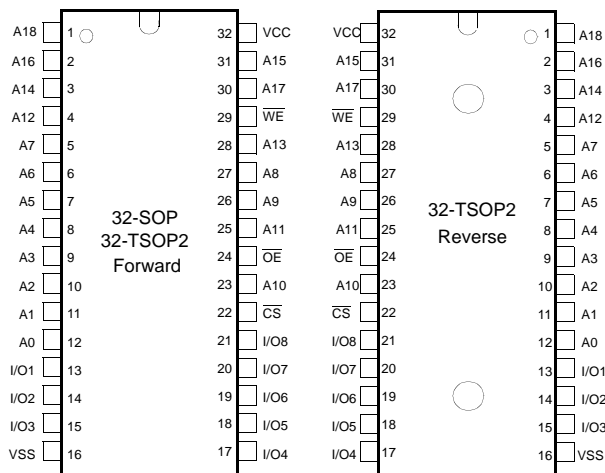
The KM68V4000B and KM68U4000B families are fabricated by SAMSUNG's advanced CMOS process technology. The families support various operating temperature range and have various package type for user flexibility of system design. The families also support low data retention voltage for battery back-up operation with low data retention current.

### PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed(ns)	Power Dissipation		PKG Type
				Standby (Isb1, Max)	Operating (Icc2)	
KM68V4000BL-L	Commercial(0~70°C)	3.0~3.6V	70 <sup>1)</sup> /85 <sup>1)</sup> /100	15μA	45mA	32-SOP 32-TSOP2-F/R
KM68V4000BLI-L	Industrial(-40~85°C)	3.0~3.6V	85 <sup>1)</sup> /100	20μA		
KM68U4000BL-L	Commercial(0~70°C)	2.7~3.3V	85 <sup>1)</sup> /100	15μA		
KM68U4000BLI-L	Industrial(-40~85°C)	2.7~3.3V	85 <sup>1)</sup> /100	20μA		

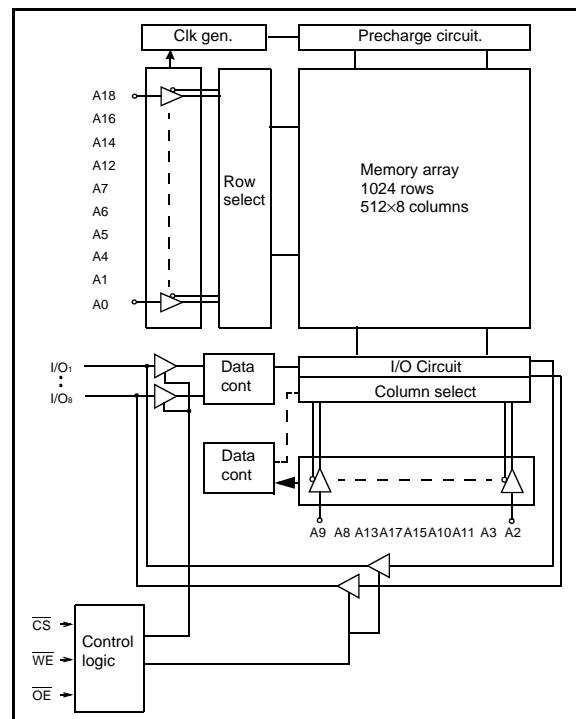
1. The parameter is measured with 30pF test load.

### PIN DESCRIPTION



Name	Function	Name	Function
$\overline{CS}$	Chip Select Input	I/O1~I/O8	Data Inputs/Outputs
$\overline{OE}$	Output Enable Input	Vcc	Power
$\overline{WE}$	Write Enable Input	Vss	Ground
A0~A18	Address Inputs		

### FUNCTIONAL BLOCK DIAGRAM



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## PRODUCT LIST

Commercial Temp Products(0~70°C)		Industrial Temp Products(-40~85°C)	
Part Name	Function	Part Name	Function
KM68V4000BLG-7L	32-SOP, 70ns, 3.3V,LL	KM68V4000BLGI-8L	32-SOP, 85ns, 3.3V,LL
KM68V4000BLG-8L	32-SOP, 85ns, 3.3V,LL	KM68V4000BLGI-10L	32-SOP, 100ns, 3.3V,LL
KM68V4000BLG-10L	32-SOP, 100ns, 3.3V,LL		
KM68V4000BLT-7L	32-TSOP2-F, 70ns, 3.3V,LL	KM68V4000BLTI-8L	32-TSOP2-F, 85ns, 3.3V,LL
KM68V4000BLT-8L	32-TSOP2-F, 85ns, 3.3V,LL	KM68V4000BLTI-10L	32-TSOP2-F, 100ns, 3.3V,LL
KM68V4000BLT-10L	32-TSOP2-F, 100ns, 3.3V,LL	KM68V4000BLRI-8L	32-TSOP2-R, 85ns, 3.3V,LL
KM68V4000BLR-7L	32-TSOP2-R, 70ns, 3.3V,LL	KM68V4000BLRI-10L	32-TSOP2-R, 100ns, 3.3V,LL
KM68V4000BLR-8L	32-TSOP2-R, 85ns, 3.3V,LL		
KM68V4000BLR-10L	32-TSOP2-R, 100ns, 3.3V,LL	KM68U4000BLGI-8L	32-SOP, 85ns, 3.0V,LL
		KM68U4000BLGI-10L	32-SOP, 100ns, 3.0V,LL
KM68U4000BLG-8L	32-SOP, 85ns, 3.0V,LL	KM68U4000BLTI-8L	32-TSOP2-F, 85ns, 3.0V,LL
KM68U4000BLG-10L	32-SOP, 100ns, 3.0V,LL	KM68U4000BLTI-10L	32-TSOP2-F, 100ns, 3.0V,LL
		KM68U4000BLRI-8L	32-TSOP2-R, 85ns, 3.0V,LL
KM68U4000BLT-8L	32-TSOP2-F, 85ns, 3.0V,LL	KM68U4000BLRI-10L	32-TSOP2-R, 100ns, 3.0V,LL
KM68U4000BLT-10L	32-TSOP2-F, 100ns, 3.0V,LL		
KM68U4000BLR-8L	32-TSOP2-R, 85ns, 3.0V,LL		
KM68U4000BLR-10L	32-TSOP2-R, 100ns, 3.0V,LL		

Note : LL means Low Low standby current

## FUNCTIONAL DESCRIPTION

CS	OE	WE	I/O	Mode	Power
H	X <sup>1)</sup>	X <sup>1)</sup>	High-Z	Deselected	Standby
L	H	H	High-Z	Output Disabled	Active
L	L	H	Dout	Read	Active
L	X <sup>1)</sup>	L	Din	Write	Active

1. X means don't care (Must be in low or high state)

## ABSOLUTE MAXIMUM RATINGS<sup>1)</sup>

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	V <sub>IN</sub> ,V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> +0.5	V	-
Voltage on Vcc supply relative to Vss	V <sub>CC</sub>	-0.3 to 4.6	V	-
Power Dissipation	P <sub>D</sub>	1	W	-
Storage temperature	T <sub>STG</sub>	-65 to 150	°C	-
Operating Temperature	T <sub>A</sub>	0 to 70	°C	KM68V4000BL, KM68U4000BL
		-40 to 85	°C	KM68V4000BLI, KM68U4000BLI
Soldering temperature and time	T <sub>SOLDER</sub>	260°C, 10sec (Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## RECOMMENDED DC OPERATING CONDITIONS<sup>1)</sup>

Item	Symbol	Product	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	KM68V4000B Family KM68U4000B Family	3.0 2.7	3.3 3.0	3.6 3.3	V
Ground	V <sub>SS</sub>	All Family	0	0	0	V
Input high voltage	V <sub>IH</sub>	KM68V4000B, KM68U4000B Family	2.2	-	V <sub>CC</sub> +0.3 <sup>2)</sup>	V
Input low voltage	V <sub>IL</sub>	KM68V4000B, KM68U4000B Family	-0.3 <sup>3)</sup>	-	0.6	V

Note:

1. Commercial Product : T<sub>A</sub>=0 to 70°C, otherwise specified

Industrial Product : T<sub>A</sub>=-40 to 85°C, otherwise specified

2. Overshoot : V<sub>CC</sub>+3.0V in case of pulse width ≤ 30ns

3. Undershoot : -3.0V in case of pulse width ≤ 30ns

4. Overshoot and undershoot are sampled, not 100% tested.

## CAPACITANCE<sup>1)</sup> (f=1MHz, T<sub>A</sub>=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	8	pF
Input/Output capacitance	C <sub>IO</sub>	V <sub>IO</sub> =0V	-	10	pF

1. Capacitance is sampled, not 100% tested

## DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA
Output leakage current	I <sub>LO</sub>	$\overline{CS}$ =V <sub>IH</sub> or $\overline{OE}$ =V <sub>IH</sub> or $\overline{WE}$ =V <sub>IL</sub> V <sub>IO</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA
Operating power supply	I <sub>CC</sub>	I <sub>IO</sub> =0mA, $\overline{CS}$ =V <sub>IL</sub> , V <sub>IN</sub> =V <sub>IL</sub> or V <sub>IH</sub> , Read	-	-	10	mA
Average operating current	I <sub>CC1</sub>	Cycle time=1μs, 100% duty, I <sub>IO</sub> =0mA, $\overline{CS}$ ≤0.2V V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	Read	-	-	10
			Write	-	-	25
	I <sub>CC2</sub>	Cycle time=Min, 100% duty, I <sub>IO</sub> =0mA, $\overline{CS}$ =V <sub>IL</sub> , V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	-	-	45	mA
Output low voltage	V <sub>OL</sub>	I <sub>OL</sub> =2.1mA	-	-	0.4	V
Output high voltage	V <sub>OH</sub>	I <sub>OH</sub> =-1.0mA	2.2	-	-	V
Standby Current(TTL)	I <sub>SB</sub>	$\overline{CS}$ =V <sub>IH</sub> , Other inputs = V <sub>IL</sub> or V <sub>IH</sub>	-	-	0.5	mA
Standby	I <sub>SB1</sub>	$\overline{CS}$ ≥V <sub>CC</sub> -0.2V, Other inputs=0~V <sub>CC</sub>	-	-	15 <sup>1)</sup>	μA

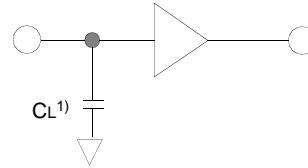
1. Industrial product = 20μA

## AC OPERATING CONDITIONS

### TEST CONDITIONS( Test Load and Input/Output Reference)

Input pulse level : 0.4 to 2.2V  
 Input rising and falling time : 5ns  
 Input and output reference voltage : 1.5V  
 Output load(see right) :  $C_L=100\text{pF}+1\text{TTL}$   
 $C_L^{(1)}=30\text{pF}+1\text{TTL}$

1. KM68V4000B-7, KM68V4000B-8 Family and KM68U4000B-8 Family



1. Including scope and jig capacitance

## AC CHARACTERISTICS

(KM68V4000B Family :  $V_{CC}=3.0\sim 3.6\text{V}$ , KM68U4000B Family :  $V_{CC}=2.7\sim 3.3\text{V}$   
 Commercial product :  $T_A=0$  to  $70^\circ\text{C}$ , Industrial product :  $T_A=-40$  to  $85^\circ\text{C}$ )

Parameter List		Symbol	Speed Bins						Units
			70ns		85ns		100ns		
			Min	Max	Min	Max	Min	Max	
Read	Read cycle time	tRC	70	-	85	-	100	-	ns
	Address access time	tAA	-	70	-	85	-	100	ns
	Chip select to output	tCO	-	70	-	85	-	100	ns
	Output enable to valid output	tOE	-	35	-	40	-	50	ns
	Chip select to low-Z output	tLZ	10	-	10	-	10	-	ns
	Output enable to low-Z output	tOLZ	5	-	5	-	5	-	ns
	Chip disable to high-Z output	tHZ	0	25	0	25	0	30	ns
	Output disable to high-Z output	tOHZ	0	25	0	25	0	30	ns
	Output hold from address change	tOH	10	-	10	-	15	-	ns
Write	Write cycle time	tWC	70	-	85	-	100	-	ns
	Chip select to end of write	tCW	60	-	70	-	80	-	ns
	Address set-up time	tAS	0	-	0	-	0	-	ns
	Address valid to end of write	tAW	60	-	70	-	80	-	ns
	Write pulse width	tWP	55	-	55	-	70	-	ns
	Write recovery time	tWR	0	-	0	-	0	-	ns
	Write to output high-Z	tWHZ	0	25	0	25	0	30	ns
	Data to write time overlap	tDW	30	-	35	-	40	-	ns
	Data hold from write time	tDH	0	-	0	-	0	-	ns
	End write to output low-Z	tOW	5	-	5	-	5	-	ns

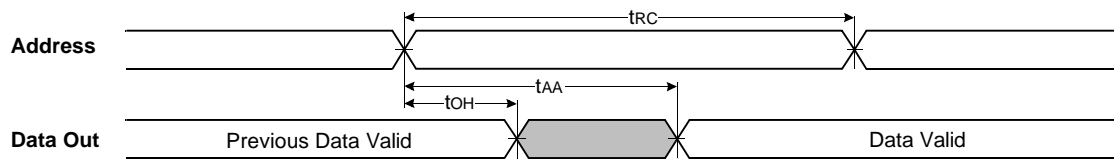
## DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit
V <sub>CC</sub> for data retention	V <sub>DR</sub>	$\overline{CS} \geq V_{CC}-0.2\text{V}$	2.0	-	3.6	V
Data retention current	I <sub>DR</sub>	$V_{CC}=3.0\text{V}$ , $\overline{CS} \geq V_{CC}-0.2\text{V}$	-	0.5	15 <sup>1)</sup>	μA
Data retention set-up time	t <sub>SDR</sub>	See data retention waveform	0	-	-	ms
Recovery time	t <sub>RDR</sub>		5	-	-	

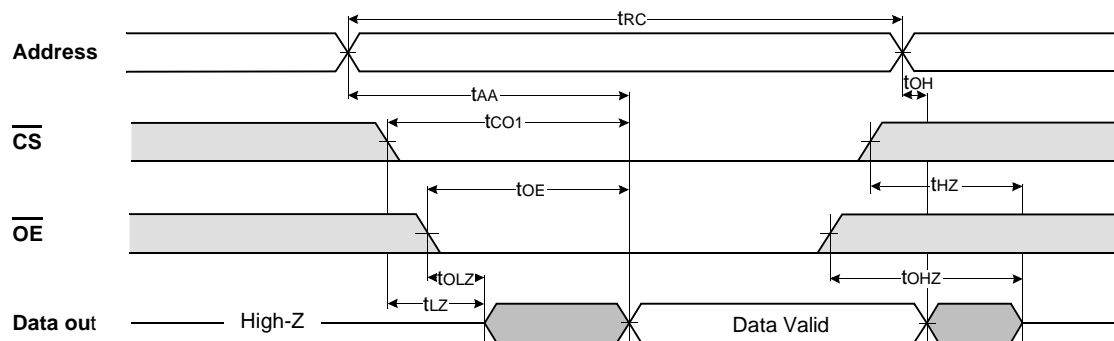
1. Industrial product = 20μA

## TIMMING DIAGRAMS

**TIMING WAVEFORM OF READ CYCLE(1)** (Address Controlled,  $\overline{CS}=\overline{OE}=V_{IL}$ ,  $\overline{WE}=V_{IH}$ )



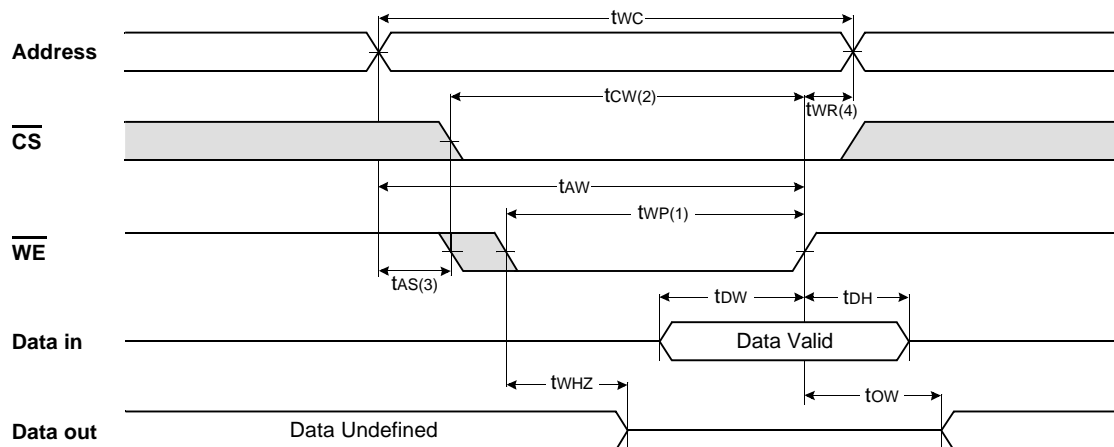
**TIMING WAVEFORM OF READ CYCLE(2)** ( $\overline{WE}=V_{IH}$ )



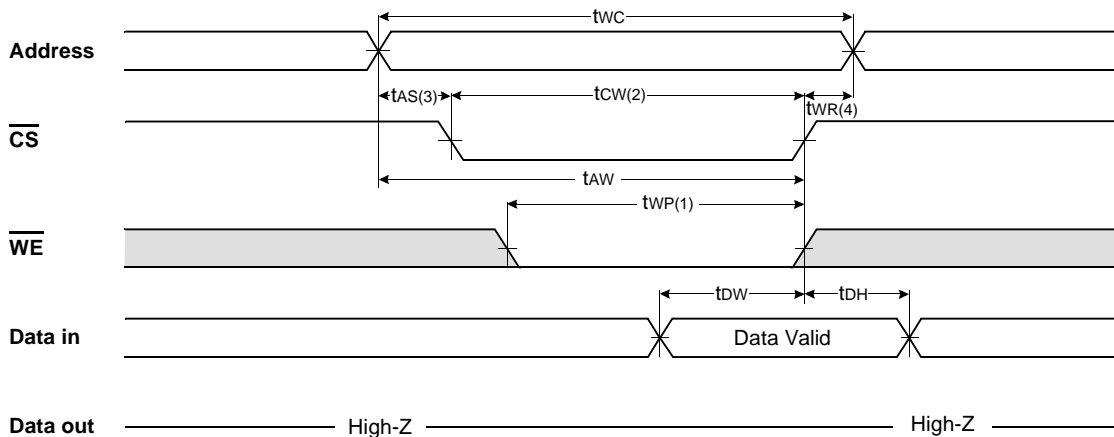
### NOTES (READ CYCLE)

1.  $t_{HZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition,  $t_{HZ}(\text{Max.})$  is less than  $t_{LZ}(\text{Min.})$  both for a given device and from device to device interconnection.

## TIMING WAVEFORM OF WRITE CYCLE(1) ( $\overline{WE}$ Controlled)



## TIMING WAVEFORM OF WRITE CYCLE(2) ( $\overline{CS}$ Controlled)

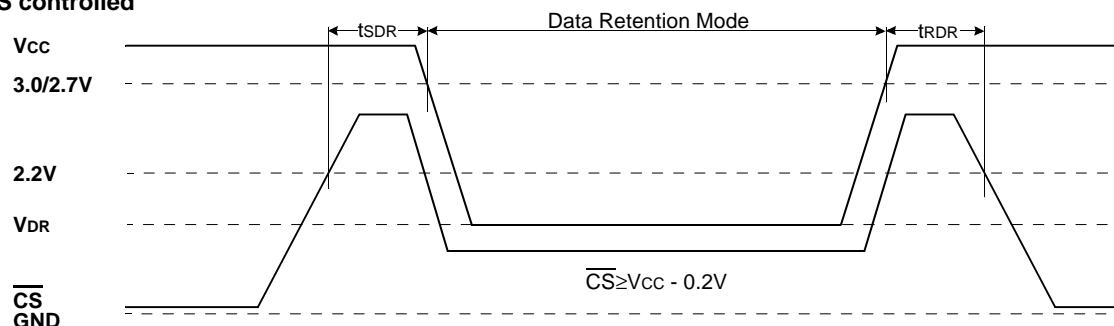


### NOTES (WRITE CYCLE)

1. A write occurs during the overlap of a low  $\overline{CS}$  and a low  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CS}$  going Low and  $\overline{WE}$  going low : A write end at the earliest transition among  $\overline{CS}$  going high and  $\overline{WE}$  going high,  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{CW}$  is measured from the  $\overline{CS}$  going low to end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.  $t_{WR}$  applied in case a write ends as  $\overline{CS}$  or  $\overline{WE}$  going high.

## DATA RETENTION WAVE FORM

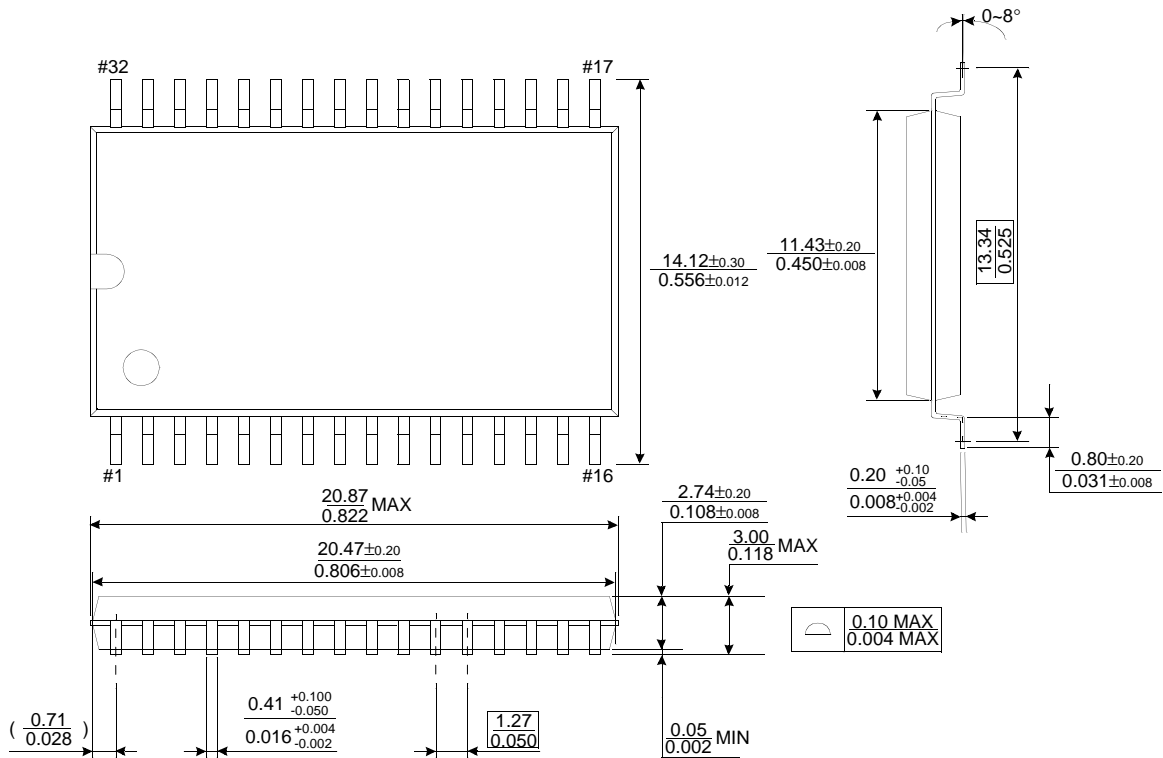
### $\overline{CS}$ controlled



## PACKAGE DIMENSIONS

Units : millimeter(inch)

### 32 PIN PLASTIC SMALL OUTLINE PACKAGE (525mil)

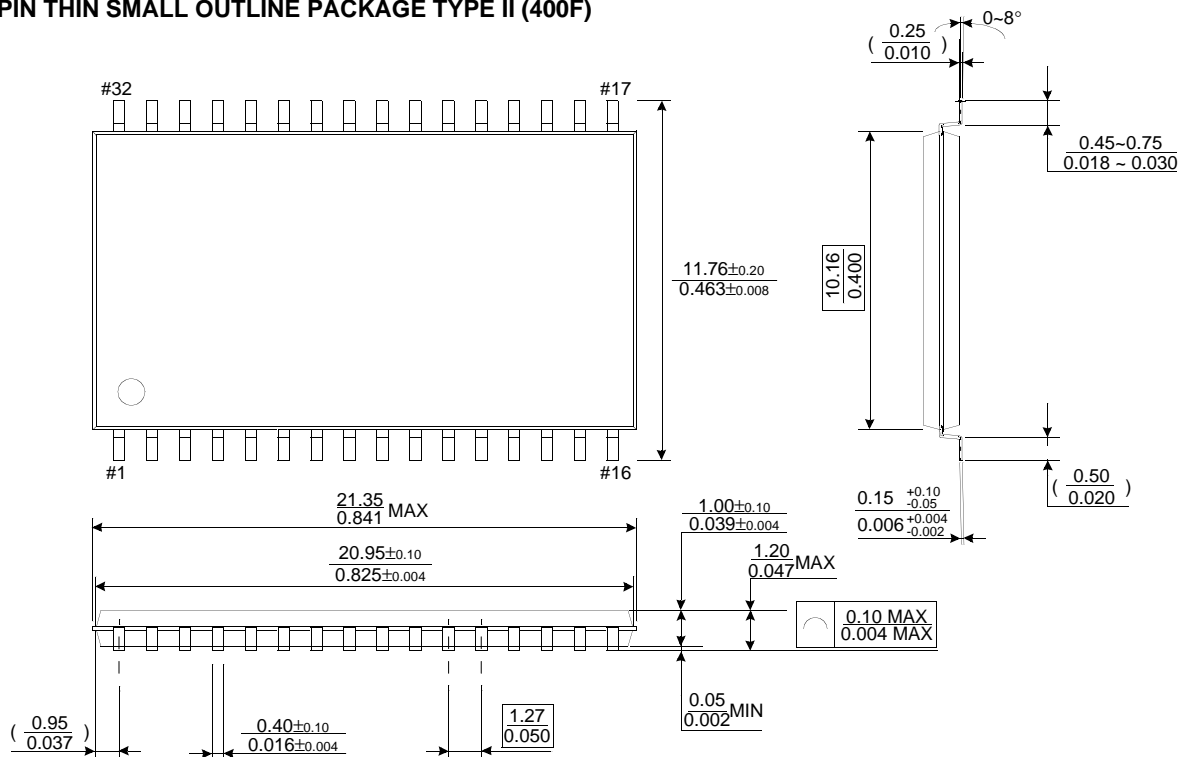




## PACKAGE DIMENSIONS

Units : millimeter(inch)

### 32 PIN THIN SMALL OUTLINE PACKAGE TYPE II (400F)



### 32 PIN THIN SMALL OUTLINE PACKAGE TYPE II (400R)

